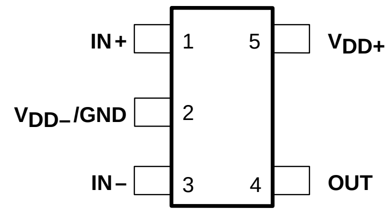
- **Output Swing Includes Both Supply Rails**
- **Low Noise . . . 15 nV/√Hz Typ at f = 1 kHz**
- **Low Input Bias Current . . . 1 pA Typ**
- **Fully Specified for Single-Supply 3-V and 5-V Operation**
- **Common-Mode Input Voltage Range Includes Negative Rail**
- **High Gain Bandwidth . . . 2 MHz at V_{DD} = 5 V With 600-Ω Load**
- **High Slew Rate . . . 1.6 V/μs at V_{DD} = 5 V**
- **Wide Supply Voltage Range 2.7 V to 10 V**
- **Macromodel Included**

**DBV PACKAGE
(TOP VIEW)**



description

The TLV2231 is a single low-voltage operational amplifier available in the SOT-23 package. It offers 2 MHz of bandwidth and 1.6 V/μs of slew rate for applications requiring good ac performance. The device exhibits rail-to-rail output performance for increased dynamic range in single or split supply applications. The TLV2231 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2231, exhibiting high input impedance and low noise, is excellent for small-signal conditioning of high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single- or split-supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). The device can also drive 600-Ω loads for telecom applications.

With a total area of 5.6mm^2, the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces. TI has also taken special care to provide a pinout that is optimized for board layout (see Figure 1). Both inputs are separated by GND to prevent coupling or leakage paths. The OUT and IN– terminals are on the same end of the board for providing negative feedback. Finally, gain setting resistors and the decoupling capacitor are easily placed around the package.

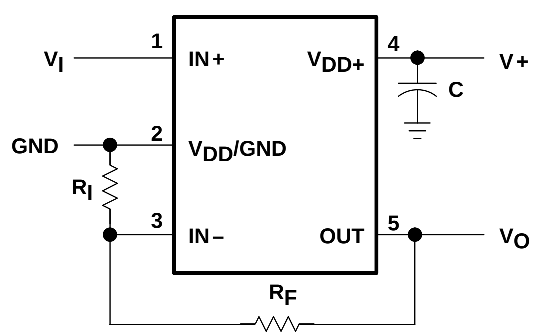


Figure 1. Typical Surface Mount Layout for a Fixed-Gain Noninverting Amplifier

AVAILABLE OPTIONS

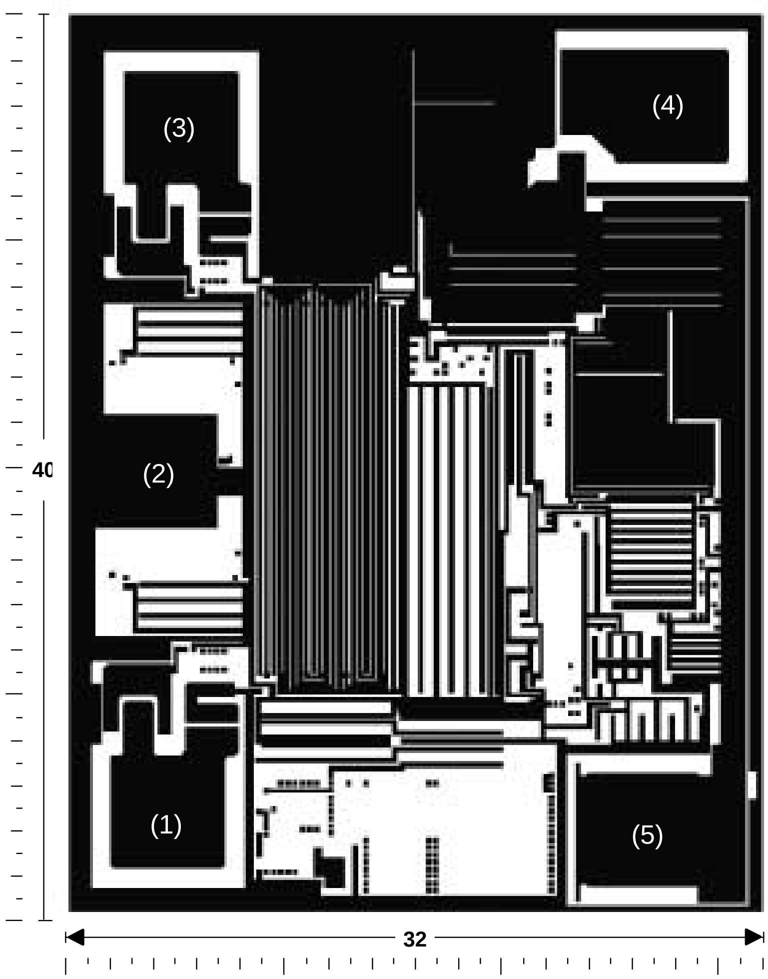
T_A	V_{IO}max AT 25°C	PACKAGED DEVICES SOT-23 (DBV)†	SYMBOL	CHIP FORM‡ (Y)
0°C to 70°C	3 mV	TLV2231CDBV	VAEC	TLV2231Y
–40°C to 85°C	3 mV	TLV2231IDBV	VAEI	

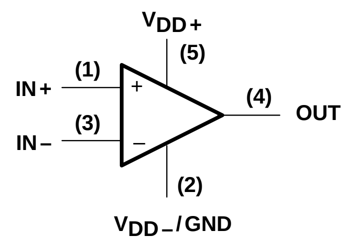
† The DBV package available in tape and reel only.
‡ Chip forms are tested at T_A = 25°C only.

TLV2231Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2231C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.

BONDING PAD ASSIGNMENTS





CHIP THICKNESS: 10 MILS TYPICAL

BONDING PADS: 4 × 4 MILS MINIMUM

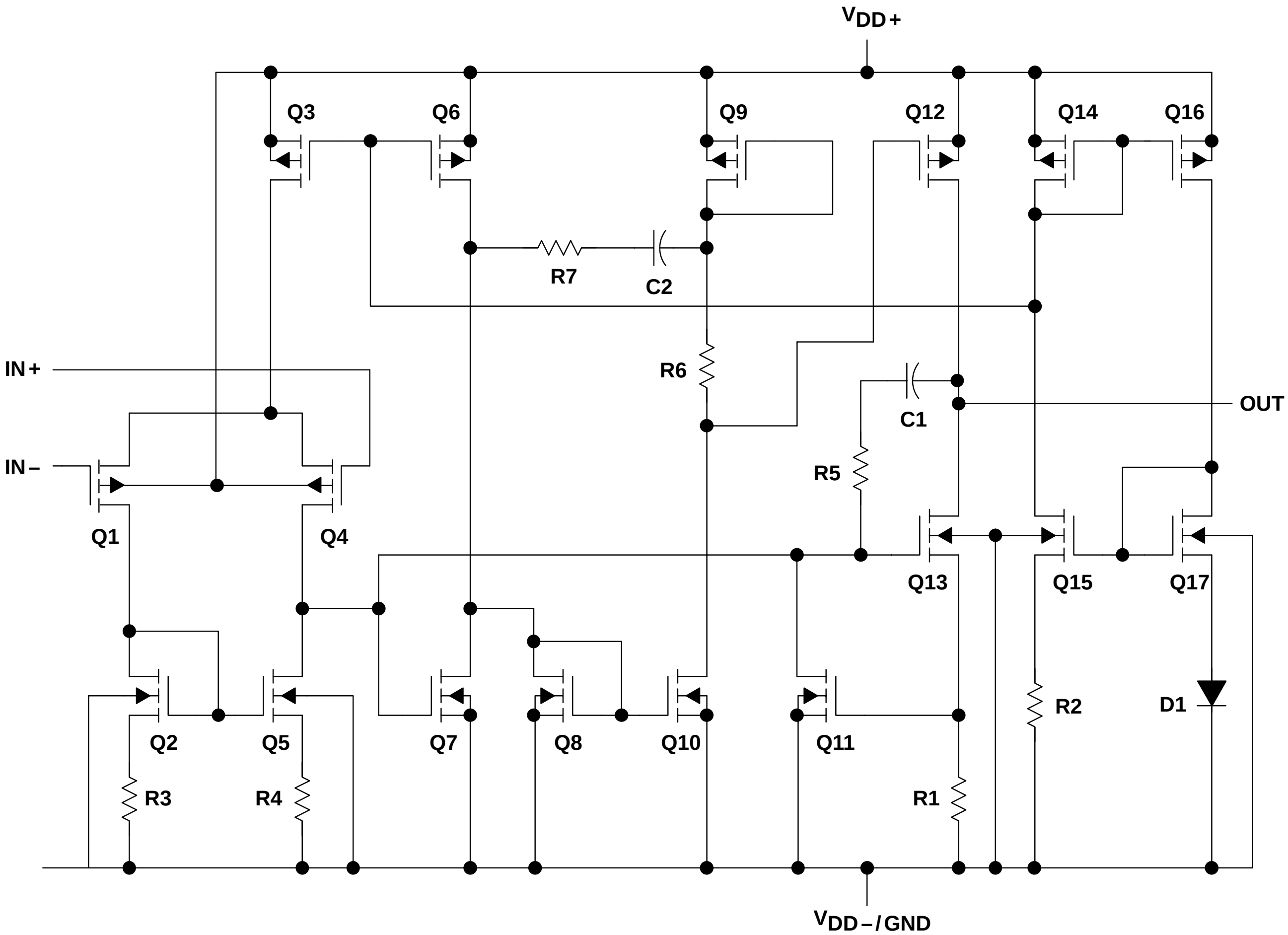
$T_J$max = 150°C

TOLERANCES ARE ±10%.

ALL DIMENSIONS ARE IN MILS.

PIN (2) IS INTERNALLY CONNECTED TO BACKSIDE OF CHIP.

equivalent schematic



COMPONENT COUNT†	
Transistors	23
Diodes	5
Resistors	11
Capacitors	2

† Includes both amplifiers and all ESD, bias, and trim circuitry

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1) .... 12 V
Differential input voltage, V_{ID} (see Note 2) .... $\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1) .... –0.3 V to V_{DD}
Input current, I_I (each input) .... ±5 mA
Output current, I_O .... ±50 mA
Total current into V_{DD+} .... ±50 mA
Total current out of V_{DD-} .... ±50 mA
Duration of short-circuit current (at or below) 25°C (see Note 3) .... unlimited
Continuous total power dissipation .... See Dissipation Rating Table
Operating free-air temperature range, T_A: TLV2231C .... 0°C to 70°C
TLV2231I .... –40°C to 85°C
Storage temperature range, T_{stg} .... –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package .... 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-}.
2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below V_{DD-} – 0.3 V.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

recommended operating conditions

	TLV2231C		TLV2231I		UNIT
	MIN	MAX	MIN	MAX	
Supply voltage, V_{DD} (see Note 1)	2.7	10	2.7	10	V
Input voltage range, V_I	V_{DD-}	V_{DD+} –1.3	V_{DD-}	V_{DD+} –1.3	V
Common-mode input voltage, V_{IC}	V_{DD-}	V_{DD+} –1.3	V_{DD-}	V_{DD+} –1.3	V
Operating free-air temperature, T_A	0	70	–40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-}.

electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	TLV2231C MIN	TLV2231C TYP	TLV2231C MAX	TLV2231I MIN	TLV2231I TYP	TLV2231I MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD\pm} = \pm1.5$ V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	Full range		0.75	3		0.75	3	mV
α_{VIO}	Temperature coefficient of input offset voltage		Full range		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)		25°C		0.003			0.003		μV/mo
I_{IO}	Input offset current		25°C		0.5	60		0.5	60	pA
			Full range			150			150	
I_{IB}	Input bias current		25°C		1	60		1	60	pA
			Full range			150			150	
V_{ICR}	Common-mode input voltage range	R_S = 50 Ω, $\|V_{IO}\| \le 5$ mV	25°C	0 to 2	−0.3 to 2.2		0 to 2	−0.3 to 2.2		V
			Full range	0 to 1.7			0 to 1.7			
V_{OH}	High-level output voltage	I_{OH} = −1 mA	25°C		2.87			2.87		V
		I_{OH} = −2 mA	25°C		2.74			2.74		
			Full range	2			2			
V_{OL}	Low-level output voltage	V_{IC} = 1.5 V, I_{OL} = 50 μA	25°C		10			10		mV
		V_{IC} = 1.5 V, I_{OL} = 500 μA	25°C		100			100		
			Full range			300			300	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 1.5 V, V_O = 1 V to 2 V, R_L = 600 Ω‡	25°C	1	1.6		1	1.6		V/mV
			Full range	0.3			0.3			
		V_{IC} = 1.5 V, V_O = 1 V to 2 V, R_L = 1 MΩ‡	25°C		250			250		
r_{id}	Differential input resistance		25°C		10^{12}			10^{12}		Ω
r_{ic}	Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
c_{ic}	Common-mode input capacitance	f = 10 kHz	25°C		6			6		pF
z_o	Closed-loop output impedance	f = 1 MHz, A_V = 1	25°C		156			156		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 1.7 V, V_O = 1.5 V, R_S = 50 Ω	25°C	60	70		60	70		dB
			Full range	55			55			
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V, $V_{IC} = V_{DD}/2$, No load	25°C	70	96		70	96		dB
			Full range	70			70			
I_{DD}	Supply current	V_O = 1.5 V, No load	25°C		750	1200		750	1200	μA
			Full range			1500			1500	

† Full range for the TLV2231C is 0°C to 70°C. Full range for the TLV2231I is – 40°C to 85°C.
‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at specified free-air temperature, V_{DD} = 3 V

PARAMETER		TEST CONDITIONS		T_A†	TLV2231C MIN	TLV2231C TYP	TLV2231C MAX	TLV2231I MIN	TLV2231I TYP	TLV2231I MAX	UNIT
SR	Slew rate at unity gain	V_O = 1.1 V to 1.9 V, R_L = 600 Ω‡, C_L = 100 pF‡		25°C	0.75	1.25		0.75	1.25		V/μs
				Full range	0.5			0.5			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		105			105		nV/√Hz
		f = 1 kHz		25°C		16			16		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		1.4			1.4		μV
		f = 0.1 Hz to 10 Hz		25°C		1.5			1.5		
I_n	Equivalent input noise current			25°C		0.6			0.6		fA /√Hz
THD+N	Total harmonic distortion plus noise	V_O = 1 V to 2 V, f = 20 kHz, R_L = 600 Ω‡	A_V = 1	25°C		0.285%			0.285%		
			A_V = 10			7.2%			7.2%		
		V_O = 1 V to 2 V, f = 20 kHz, R_L = 600 Ω§	A_V = 1	25°C		0.014%			0.014%		
			A_V = 10			0.098%			0.098%		
			A_V = 100			0.13%			0.13%		
	Gain-bandwidth product	f = 10 kHz, R_L = 600 Ω‡, C_L = 100 pF‡		25°C		1.9			1.9		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 1 V, A_V = 1, R_L = 600 Ω‡, C_L = 100 pF‡		25°C		60			60		kHz
t_s	Settling time	A_V = –1, Step = 1 V to 2 V, R_L = 600 Ω‡, C_L = 100 pF‡	To 0.1%	25°C		0.9			0.9		μs
			To 0.01%			1.5			1.5		
ϕ_m	Phase margin at unity gain	R_L = 600 Ω‡, C_L = 100 pF‡		25°C		50°			50°		
	Gain margin			25°C		8			8		dB

† Full range is –40°C to 85°C.
‡ Referenced to 1.5 V
§ Referenced to 0 V

electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	TLV2231C MIN	TLV2231C TYP	TLV2231C MAX	TLV2231I MIN	TLV2231I TYP	TLV2231I MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD\pm} = \pm2.5$ V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	Full range		0.71	3		0.71	3	mV
α_{VIO}	Temperature coefficient of input offset voltage		Full range		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)		25°C		0.003			0.003		μV/mo
I_{IO}	Input offset current		25°C		0.5	60		0.5	60	pA
			Full range			150			150	
I_{IB}	Input bias current		25°C		1	60		1	60	pA
			Full range			150			150	
V_{ICR}	Common-mode input voltage range	R_S = 50 Ω, $\|V_{IO}\| \le 5$ mV	25°C	0 to 4	−0.3 to 4.2		0 to 4	−0.3 to 4.2		V
			Full range	0 to 3.7			0 to 3.7			
V_{OH}	High-level output voltage	I_{OH} = −1 mA	25°C		4.9			4.9		V
		I_{OH} = −4 mA	25°C		4.6			4.6		
			Full range	4			4			
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V, I_{OL} = 500 μA	25°C		80			80		mV
		V_{IC} = 2.5 V, I_{OL} = 1 mA	25°C		160			160		
			Full range			500			500	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 600 Ω‡	25°C	1	1.5		1	1.5		V/mV
			Full range	0.3			0.3			
		V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 1 MΩ‡	25°C		400			400		
r_{id}	Differential input resistance		25°C		10^{12}			10^{12}		Ω
r_{ic}	Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
c_{ic}	Common-mode input capacitance	f = 10 kHz	25°C		6			6		pF
z_o	Closed-loop output impedance	f = 1 MHz, A_V = 1	25°C		138			138		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 2.7 V, V_O = 2.5 V, R_S = 50 Ω	25°C	60	70		60	70		dB
			Full range	55			55			
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	V_{DD} = 4.4 V to 8 V, $V_{IC} = V_{DD}/2$, No load	25°C	70	96		70	96		dB
			Full range	70			70			
I_{DD}	Supply current	V_O = 2.5 V, No load	25°C		850	1300		850	1300	μA
			Full range			1600			1600	

† Full range for the TLV2231C is 0°C to 70°C. Full range for the TLV2231I is – 40°C to 85°C.
‡ Referenced to 2.5 V
NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at specified free-air temperature, V_{DD} = 5 V

PARAMETER		TEST CONDITIONS		T_A†	TLV2231C MIN	TLV2231C TYP	TLV2231C MAX	TLV2231I MIN	TLV2231I TYP	TLV2231I MAX	UNIT
SR	Slew rate at unity gain	V_O = 1.5 V to 3.5 V, C_L = 100 pF‡	R_L = 600 Ω‡,	25°C	1	1.6		1	1.6		V/µs
				Full range	0.7			0.7			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		100			100		nV/√Hz
		f = 1 kHz		25°C		15			15		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		1.4			1.4		µV
		f = 0.1 Hz to 10 Hz		25°C		1.5			1.5		
I_n	Equivalent input noise current			25°C		0.6			0.6		fA /√Hz
THD+N	Total harmonic distortion plus noise	V_O = 1.5 V to 3.5 V, f = 20 kHz, R_L = 600 Ω‡	A_V = 1	25°C		0.409%			0.409%		
			A_V = 10			3.68%			3.68%		
		V_O = 1.5 V to 3.5 V, f = 20 kHz, R_L = 600 Ω§	A_V = 1	25°C		0.018%			0.018%		
			A_V = 10			0.045%			0.045%		
			A_V = 100			0.116%			0.116%		
	Gain-bandwidth product	f = 10 kHz, C_L = 100 pF‡	R_L = 600 Ω‡,	25°C		2			2		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 1 V, R_L = 600 Ω‡,	A_V = 1, C_L = 100 pF‡	25°C		300			300		kHz
t_s	Settling time	A_V = –1, Step = 1.5 V to 3.5 V, R_L = 600 Ω‡, C_L = 100 pF‡	To 0.1%	25°C		0.95			0.95		µs
			To 0.01%			2.4			2.4		
ϕ_m	Phase margin at unity gain	R_L = 600 Ω‡,	C_L = 100 pF‡	25°C		48°			48°		
	Gain margin			25°C		8			8		dB

† Full range is –40°C to 85°C.
‡ Referenced to 2.5 V
§ Referenced to 0 V

electrical characteristics at V_{DD} = 3 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TLV2231Y MIN	TLV2231Y TYP	TLV2231Y MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD}\pm$ = ±1.5 V, R_S = 50 Ω	V_{IC} = 0,	V_O = 0,		750		μV
I_{IO}	Input offset current					0.5		pA
I_{IB}	Input bias current					1		pA
V_{ICR}	Common-mode input voltage range	$\|V_{IO}\| \le 5$ mV,	R_S = 50 Ω			–0.3 to 2.2		V
V_{OH}	High-level output voltage	I_{OH} = –1 mA				2.87		V
V_{OL}	Low-level output voltage	V_{IC} = 1.5 V,	I_{OL} = 50 μA			10		mV
		V_{IC} = 1.5 V,	I_{OL} = 500 μA			100		
A_{VD}	Large-signal differential voltage amplification	V_O = 1 V to 2 V	R_L = 600 Ω†			1.6		V/mV
			R_L = 1 MΩ†			250		
r_{id}	Differential input resistance					10^{12}		Ω
r_{ic}	Common-mode input resistance					10^{12}		Ω
c_{ic}	Common-mode input capacitance	f = 10 kHz				6		pF
z_o	Closed-loop output impedance	f = 1 MHz,	A_V = 1			156		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 1.7 V,	V_O = 0,	R_S = 50 Ω	60	70		dB
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V,	V_{IC} = 0,	No load		96		dB
I_{DD}	Supply current	V_O = 0,	No load			750		μA

† Referenced to 1.5 V

electrical characteristics at V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TLV2231Y MIN	TLV2231Y TYP	TLV2231Y MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD}\pm$ = ±1.5 V, R_S = 50 Ω	V_{IC} = 0,	V_O = 0,		710		μV
I_{IO}	Input offset current					0.5		pA
I_{IB}	Input bias current					1		pA
V_{ICR}	Common-mode input voltage range	$\|V_{IO}\| \le 5$ mV,	R_S = 50 Ω			–0.3 to 4.2		V
V_{OH}	High-level output voltage	I_{OH} = –1 mA				4.9		V
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V,	I_{OL} = 500 μA			80		mV
		V_{IC} = 2.5 V,	I_{OL} = 1 mA			160		
A_{VD}	Large-signal differential voltage amplification	V_O = 1 V to 2 V	R_L = 600 Ω†			15		V/mV
			R_L = 1 MΩ†			400		
r_{id}	Differential input resistance					10^{12}		Ω
r_{ic}	Common-mode input resistance					10^{12}		Ω
c_{ic}	Common-mode input capacitance	f = 10 kHz				6		pF
z_o	Closed-loop output impedance	f = 1 MHz,	A_V = 1			138		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 1.7 V,	V_O = 0,	R_S = 50 Ω	60	70		dB
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V,	V_{IC} = 0,	No load		96		dB
I_{DD}	Supply current	V_O = 0,	No load			850		μA

† Referenced to 2.5 V

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution vs Common-mode input voltage	2, 3 4, 5
α_{VIO}	Input offset voltage temperature coefficient	Distribution	6, 7
I_{IB}/I_{IO}	Input bias and input offset currents	vs Free-air temperature	8
V_I	Input voltage	vs Supply voltage vs Free-air temperature	9 10
V_{OH}	High-level output voltage	vs High-level output current	11, 14
V_{OL}	Low-level output voltage	vs Low-level output current	12, 13, 15
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	16
I_{OS}	Short-circuit output current	vs Supply voltage vs Free-air temperature	17 18
V_O	Output voltage	vs Differential input voltage	19, 20
A_{VD}	Differential voltage amplification	vs Load resistance	21
A_{VD}	Large-signal differential voltage amplification	vs Frequency vs Free-air temperature	22, 23 24, 25
z_o	Output impedance	vs Frequency	26, 27
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	28 29
k_{SVR}	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	30, 31 32
I_{DD}	Supply current	vs Supply voltage	33
SR	Slew rate	vs Load capacitance vs Free-air temperature	34 35
V_O	Inverting large-signal pulse response	vs Time	36, 37
V_O	Voltage-follower large-signal pulse response	vs Time	38, 39
V_O	Inverting small-signal pulse response	vs Time	40, 41
V_O	Voltage-follower small-signal pulse response	vs Time	42, 43
V_n	Equivalent input noise voltage	vs Frequency	44, 45
	Noise voltage (referred to input)	Over a 10-second period	46
THD + N	Total harmonic distortion plus noise	vs Frequency	47
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	48 49
	Gain margin	vs Load capacitance	50, 51
ϕ_m	Phase margin	vs Frequency vs Load capacitance	22, 23 52, 53
B_1	Unity-gain bandwidth	vs Load capacitance	54, 55

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TLV2231
INPUT OFFSET VOLTAGE

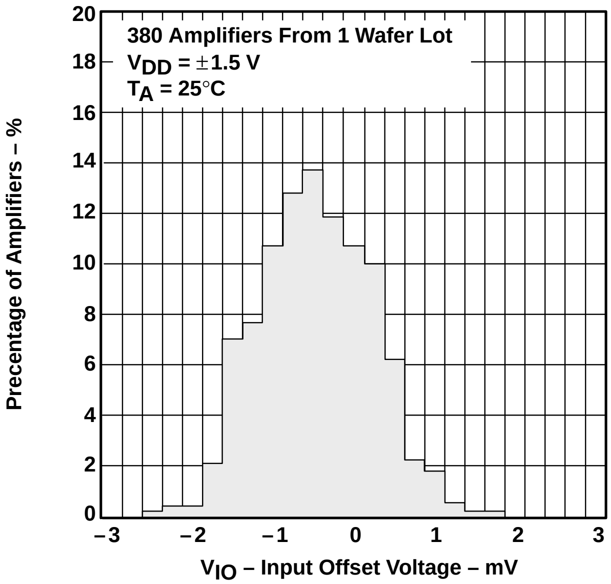


Figure 2

DISTRIBUTION OF TLV2231
INPUT OFFSET VOLTAGE

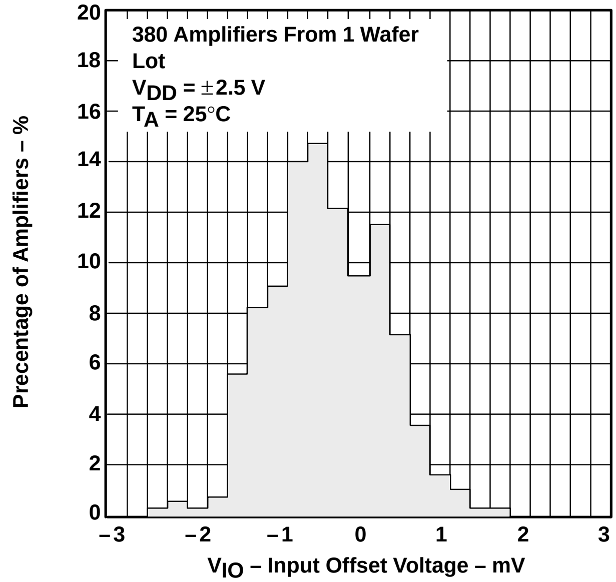


Figure 3

INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE

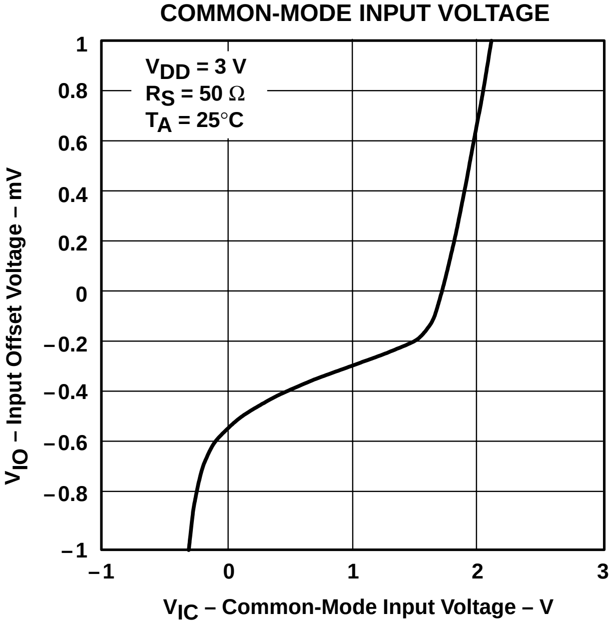


Figure 4

INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE

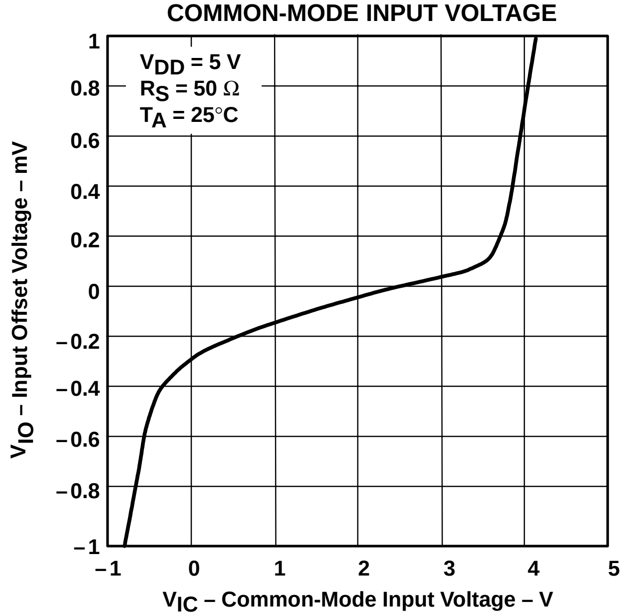


Figure 5

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

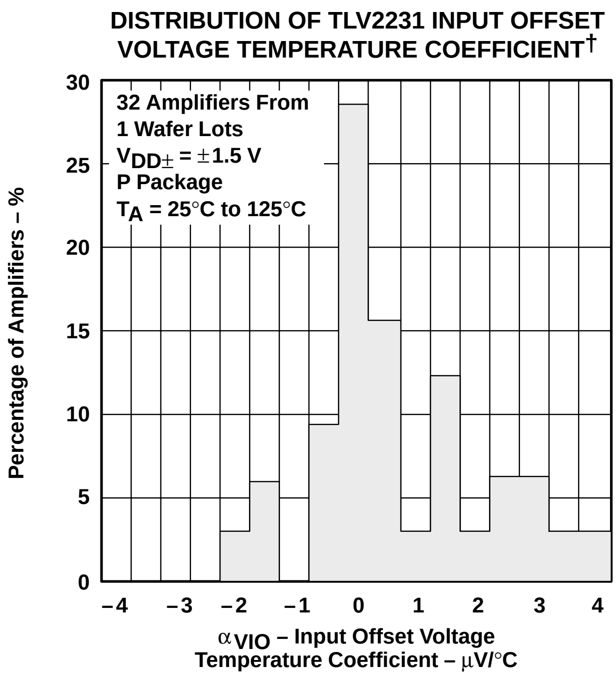


Figure 6

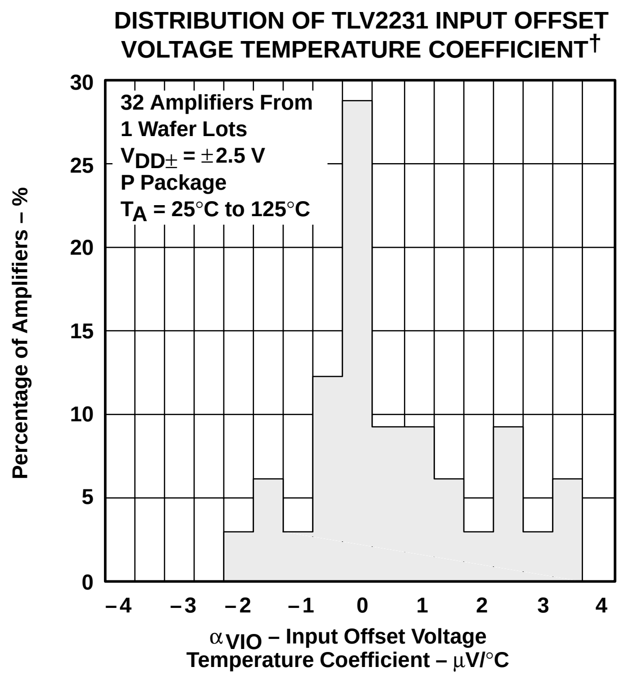


Figure 7

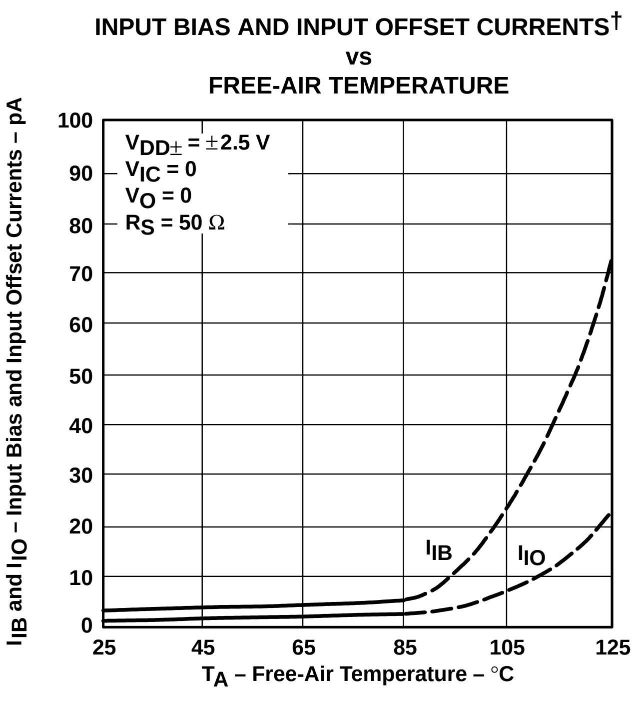


Figure 8

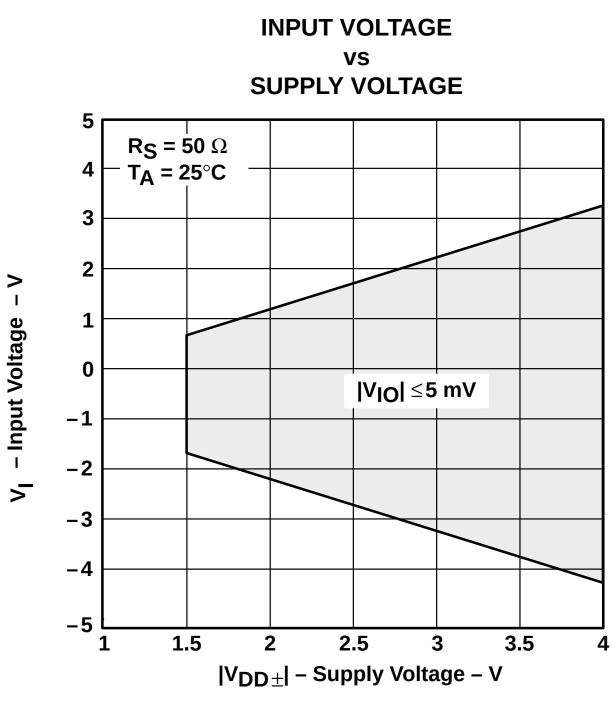


Figure 9

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

INPUT VOLTAGE† vs FREE-AIR TEMPERATURE

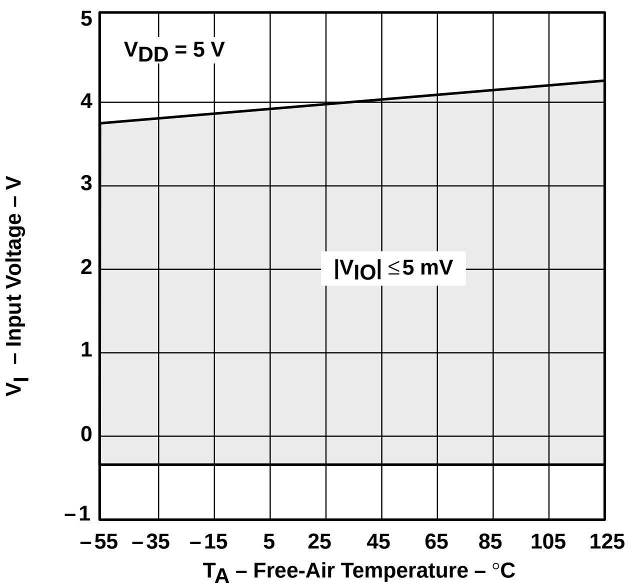


Figure 10

HIGH-LEVEL OUTPUT VOLTAGE†‡ vs HIGH-LEVEL OUTPUT CURRENT

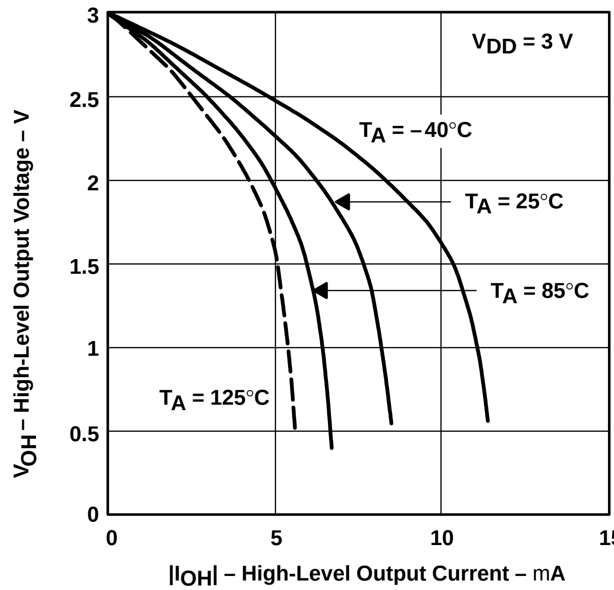


Figure 11

LOW-LEVEL OUTPUT VOLTAGE‡ vs LOW-LEVEL OUTPUT CURRENT

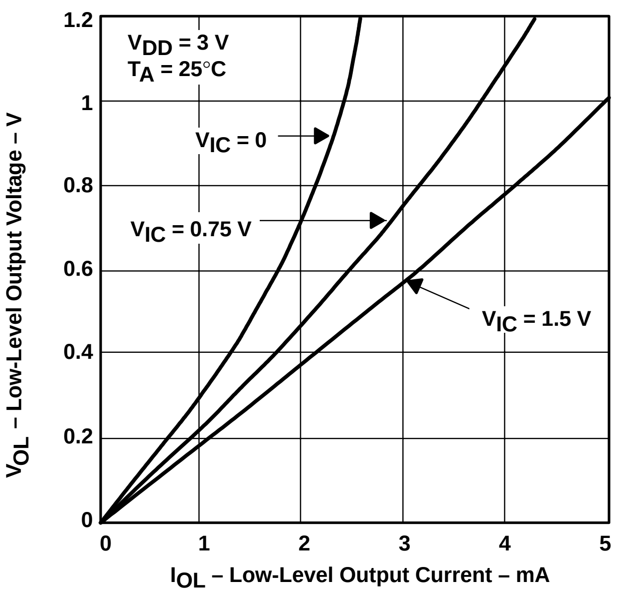


Figure 12

LOW-LEVEL OUTPUT VOLTAGE†‡ vs LOW-LEVEL OUTPUT CURRENT

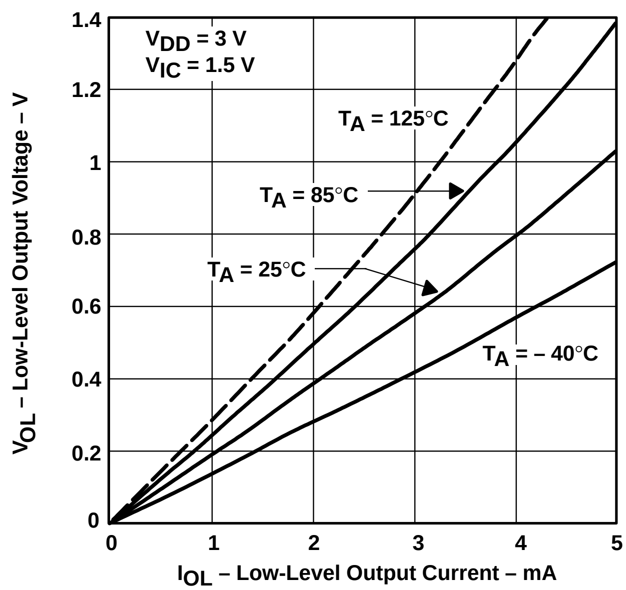


Figure 13

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

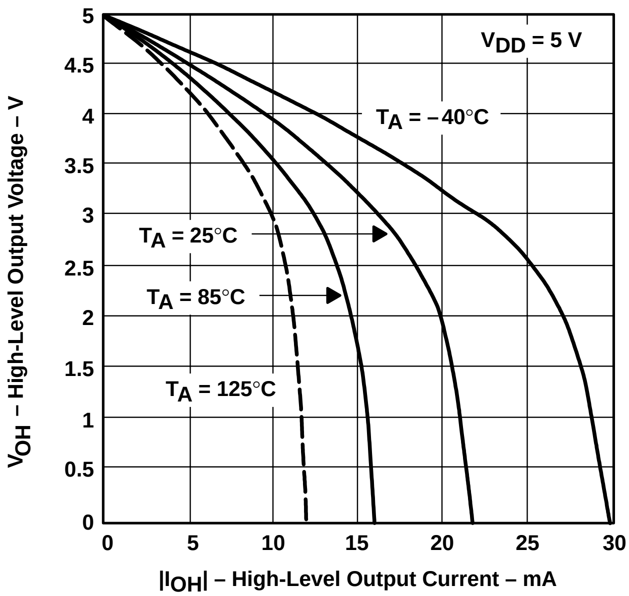


Figure 14

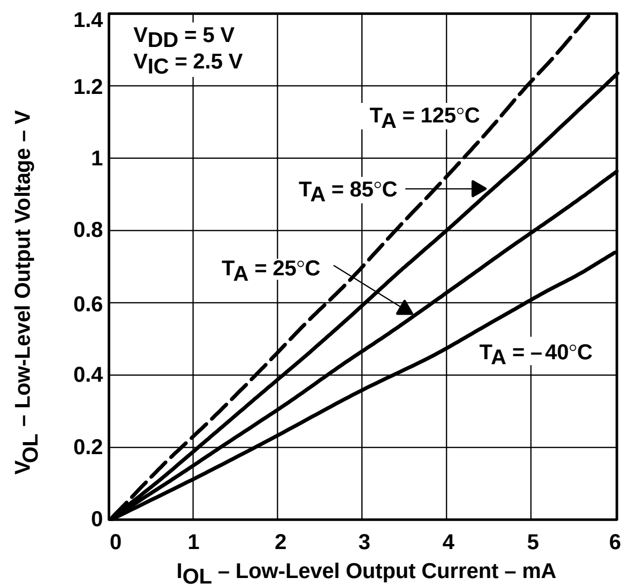


Figure 15

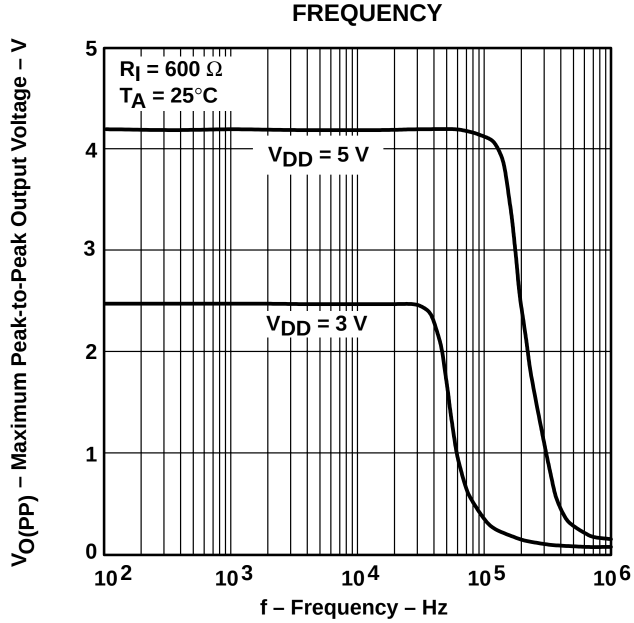


Figure 16

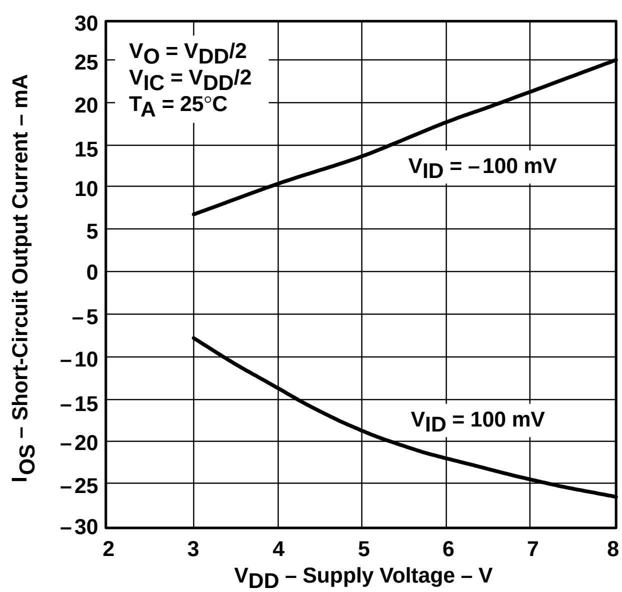


Figure 17

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

SHORT-CIRCUIT OUTPUT CURRENT†‡ vs FREE-AIR TEMPERATURE

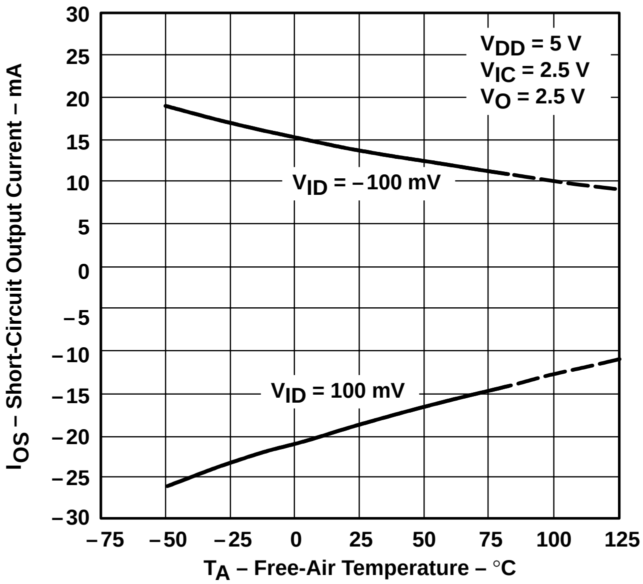


Figure 18

OUTPUT VOLTAGE‡ vs DIFFERENTIAL INPUT VOLTAGE

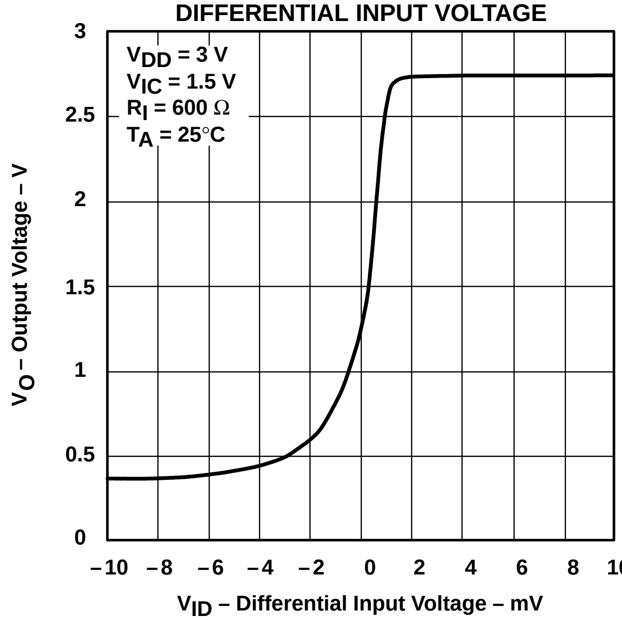


Figure 19

OUTPUT VOLTAGE‡ vs DIFFERENTIAL INPUT VOLTAGE

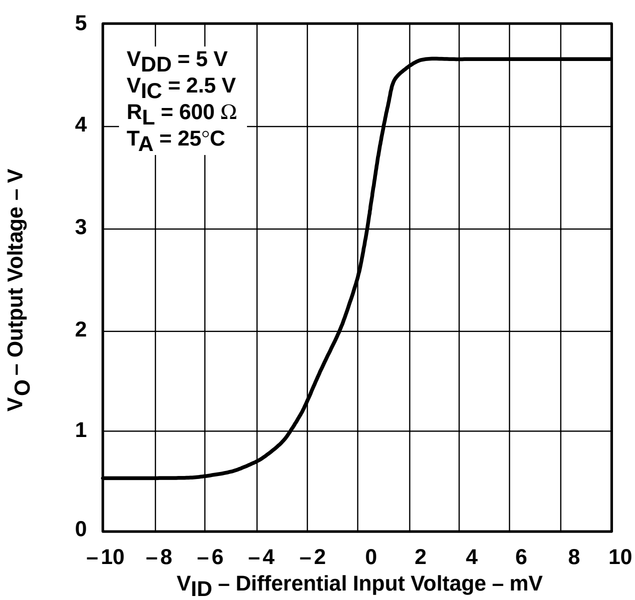


Figure 20

DIFFERENTIAL VOLTAGE AMPLIFICATION‡ vs LOAD RESISTANCE

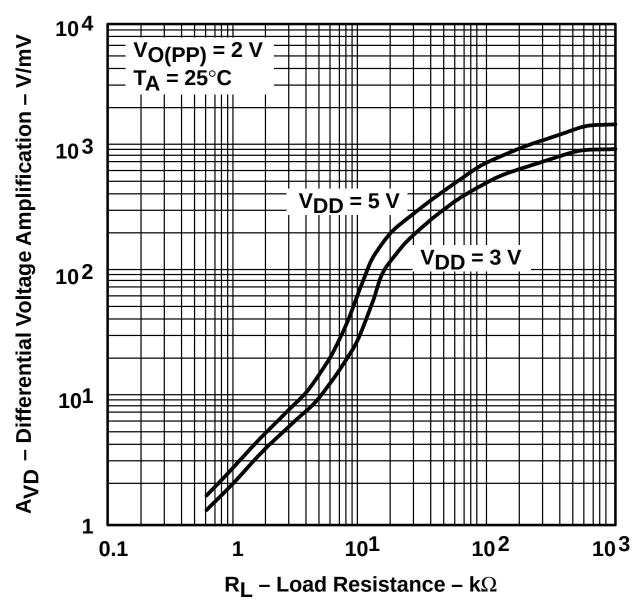


Figure 21

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN† vs FREQUENCY

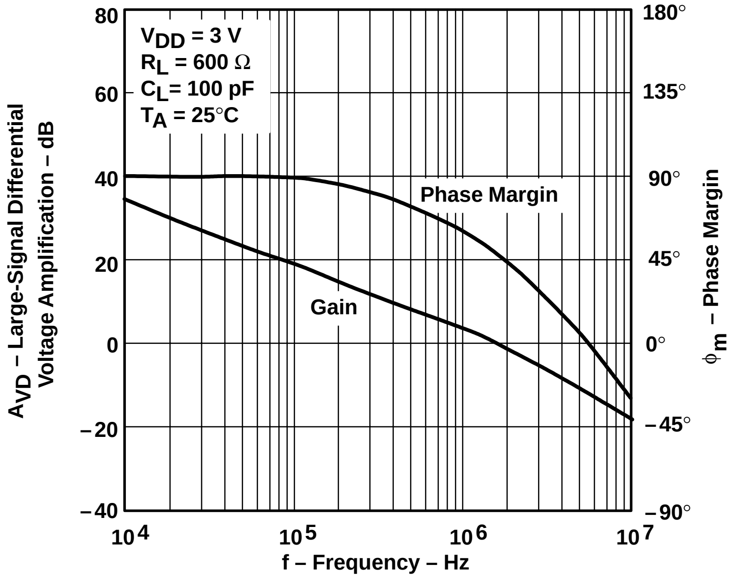


Figure 22

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN† vs FREQUENCY

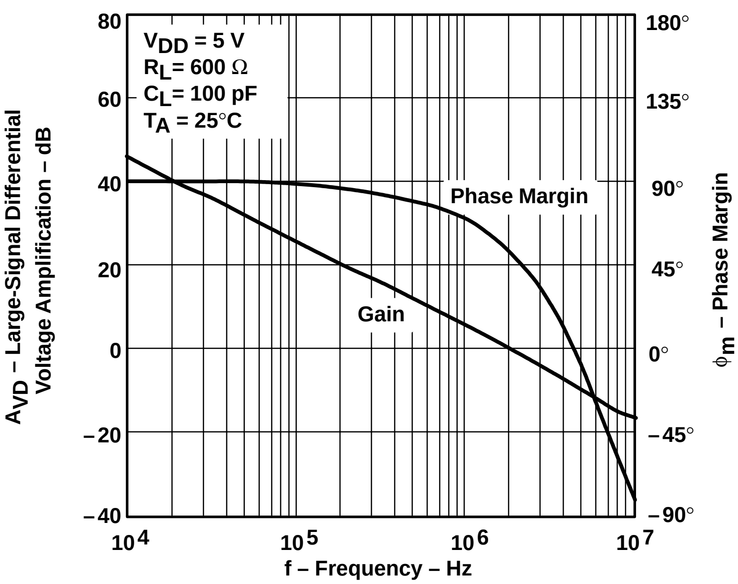


Figure 23

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION†‡ vs FREE-AIR TEMPERATURE

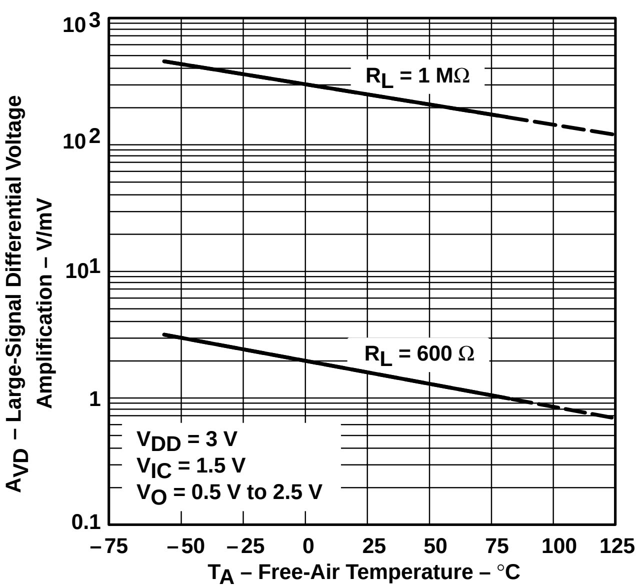


Figure 24

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION†‡ vs FREE-AIR TEMPERATURE

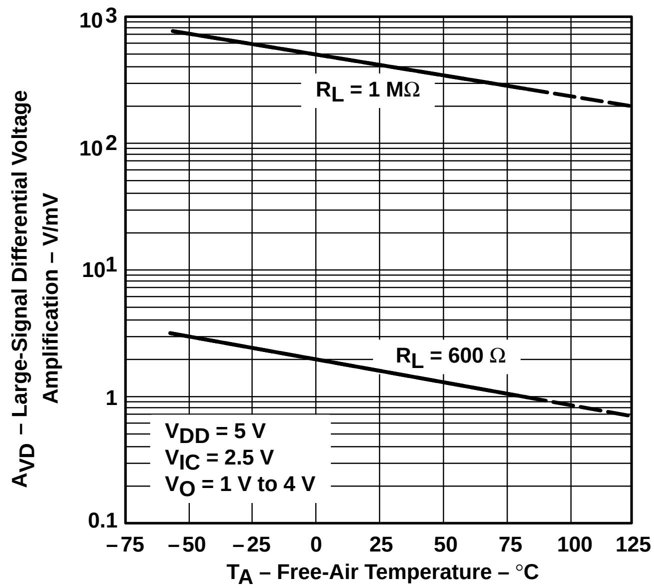


Figure 25

OUTPUT IMPEDANCE‡ vs FREQUENCY

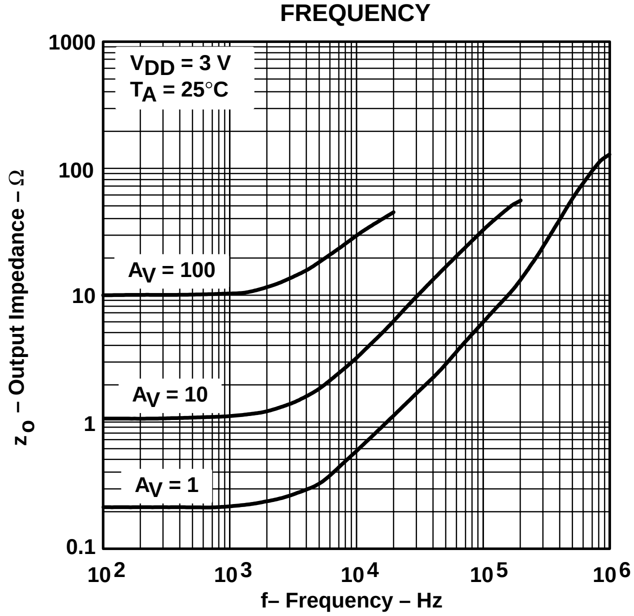


Figure 26

OUTPUT IMPEDANCE‡ vs FREQUENCY

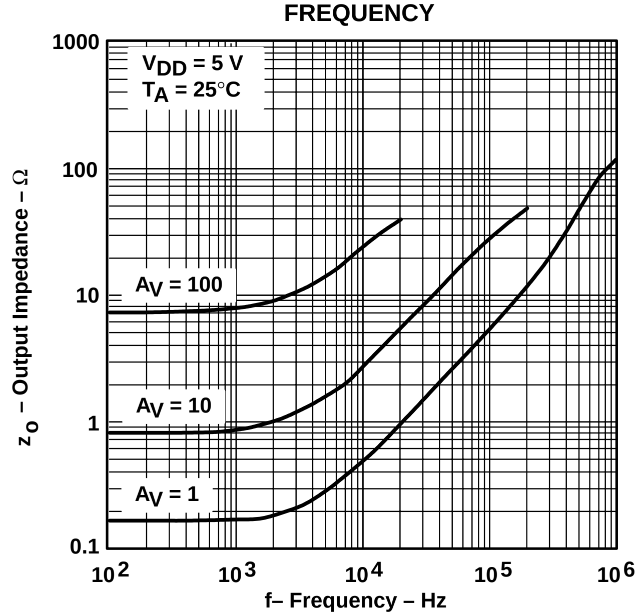


Figure 27

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

COMMON-MODE REJECTION RATIO† vs FREQUENCY

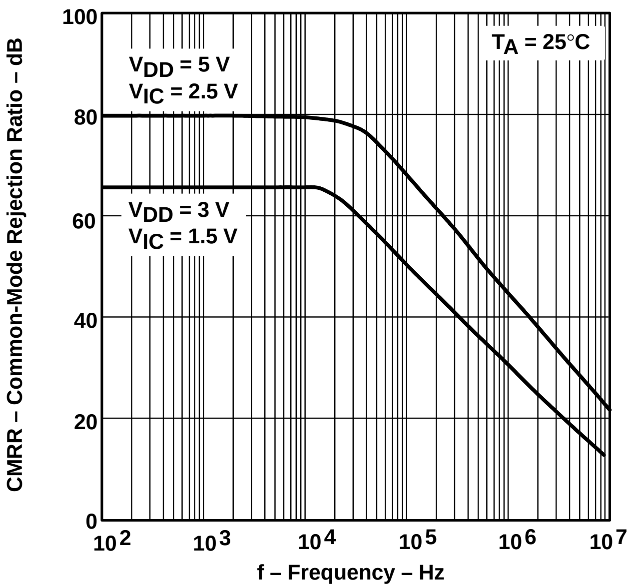


Figure 28

COMMON-MODE REJECTION RATIO†‡ vs FREE-AIR TEMPERATURE

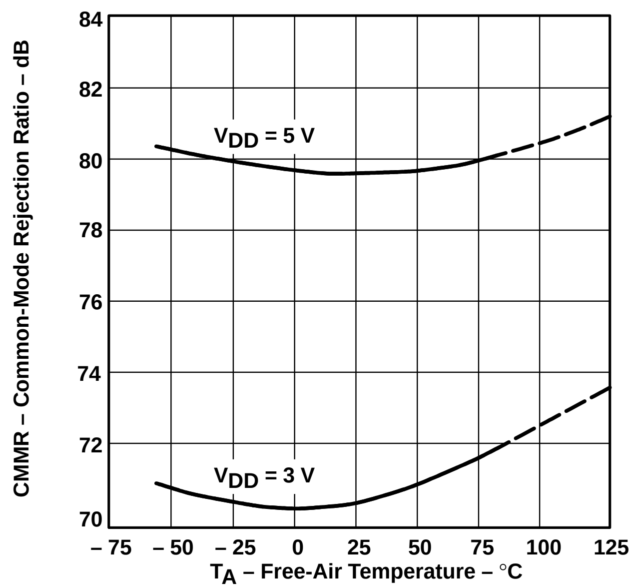


Figure 29

SUPPLY-VOLTAGE REJECTION RATIO† vs FREQUENCY

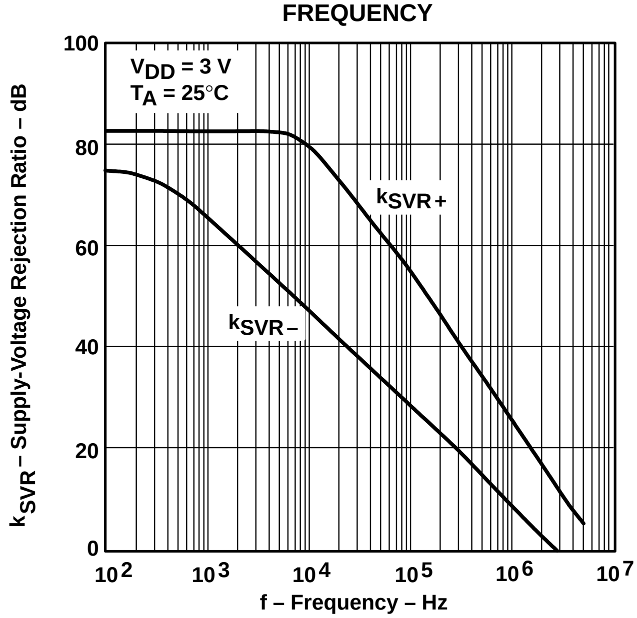


Figure 30

SUPPLY-VOLTAGE REJECTION RATIO† vs FREQUENCY

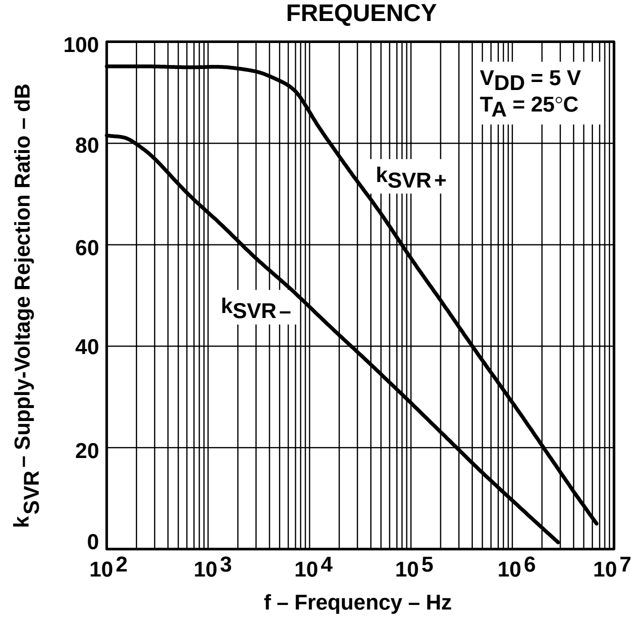


Figure 31

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.
‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

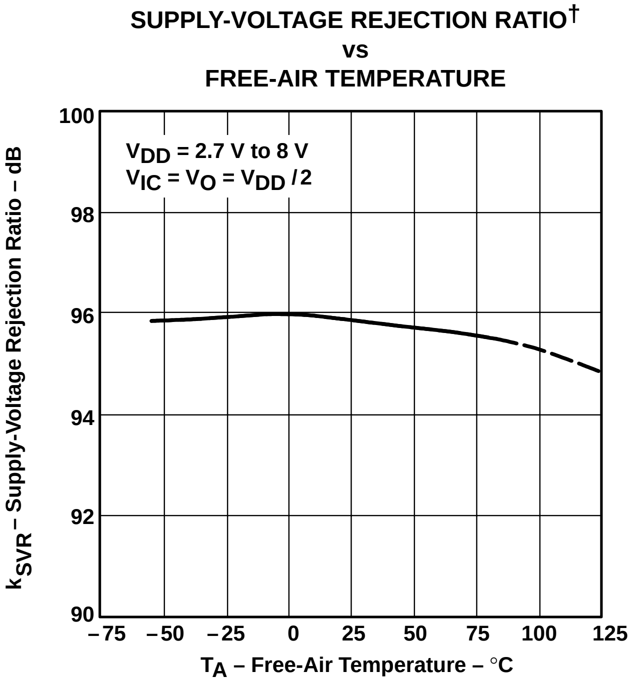


Figure 32

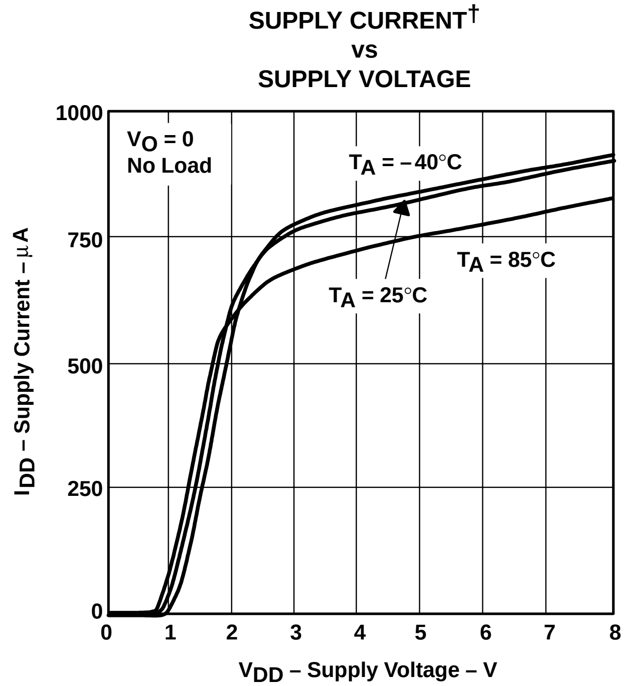


Figure 33

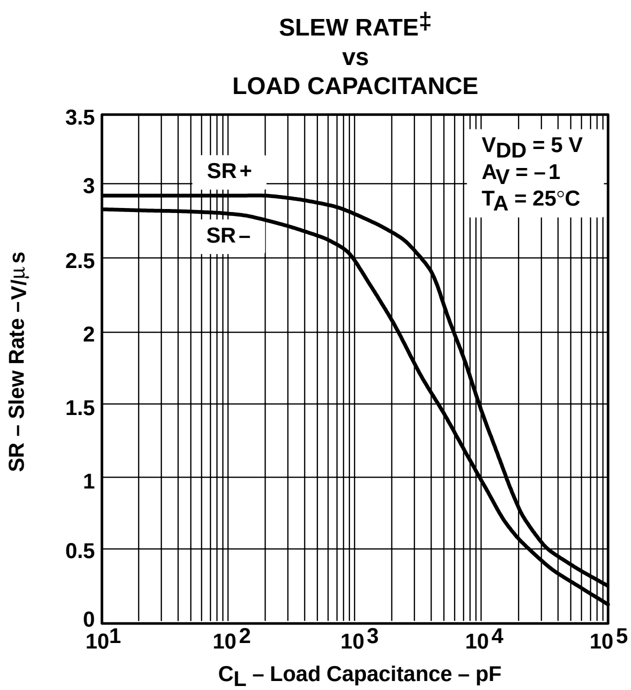


Figure 34

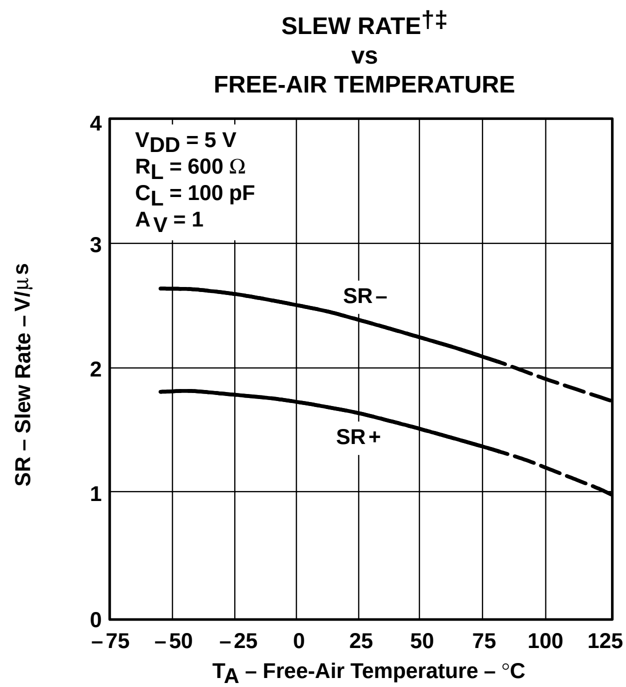


Figure 35

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

INVERTING LARGE-SIGNAL PULSE RESPONSE†

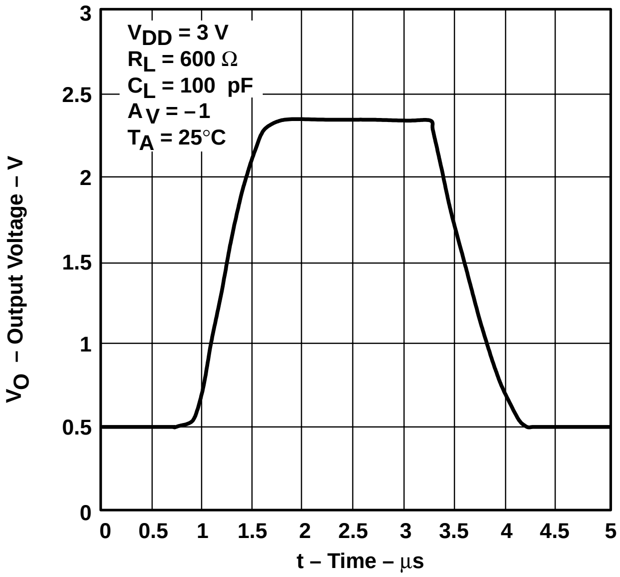


Figure 36

INVERTING LARGE-SIGNAL PULSE RESPONSE†

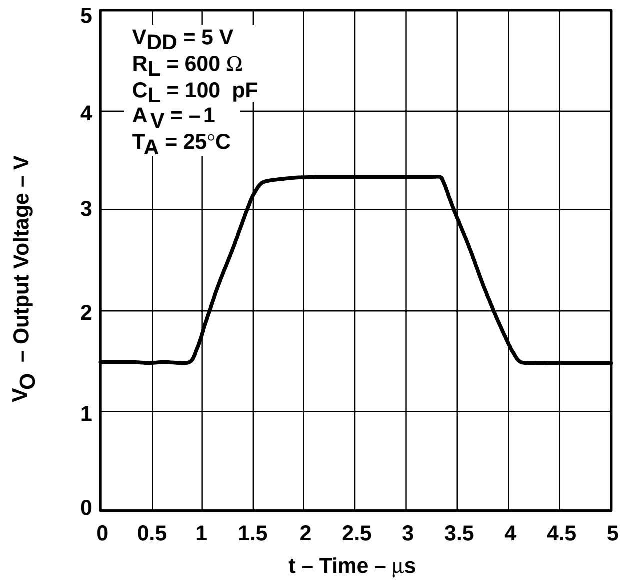


Figure 37

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

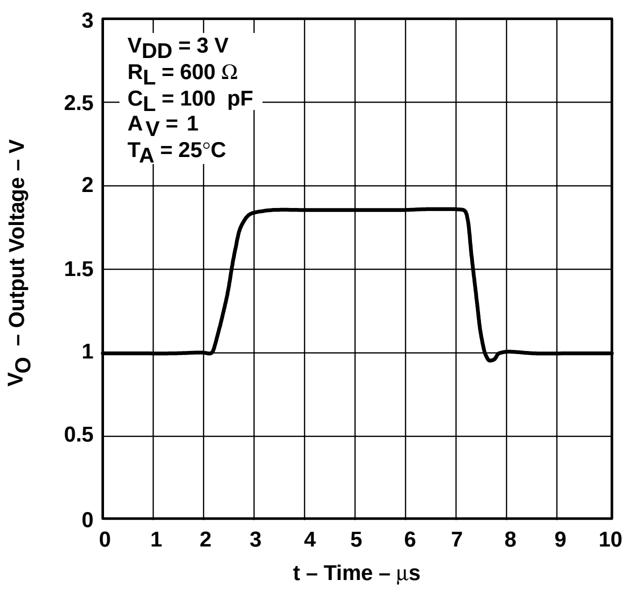


Figure 38

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

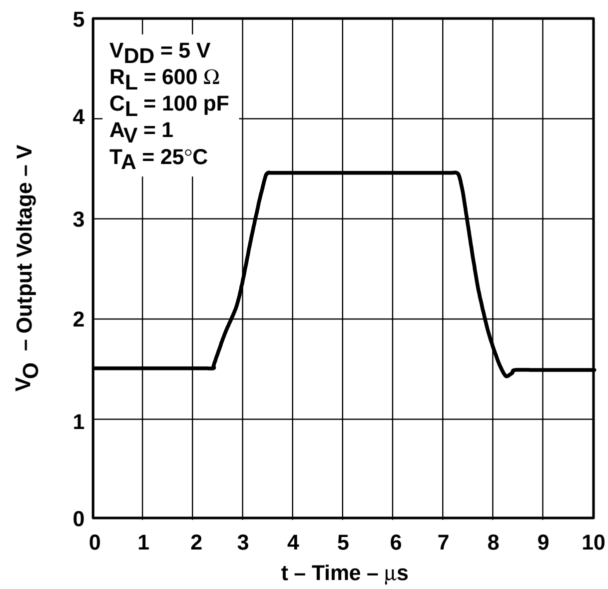


Figure 39

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

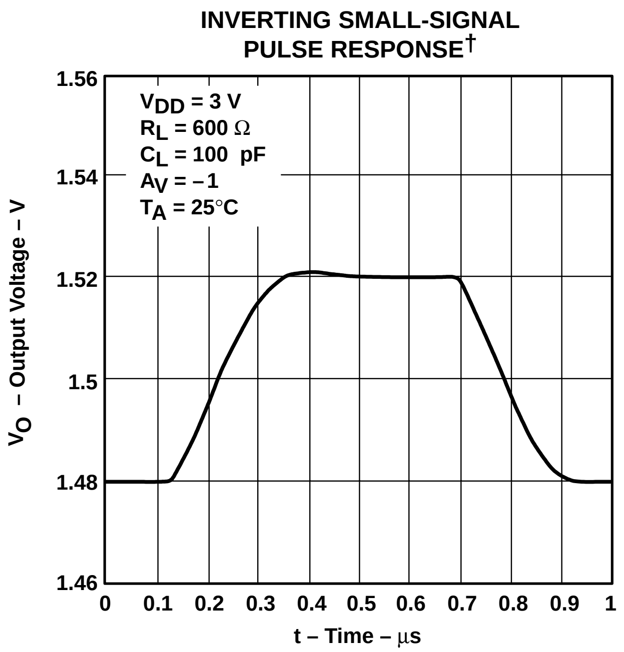


Figure 40

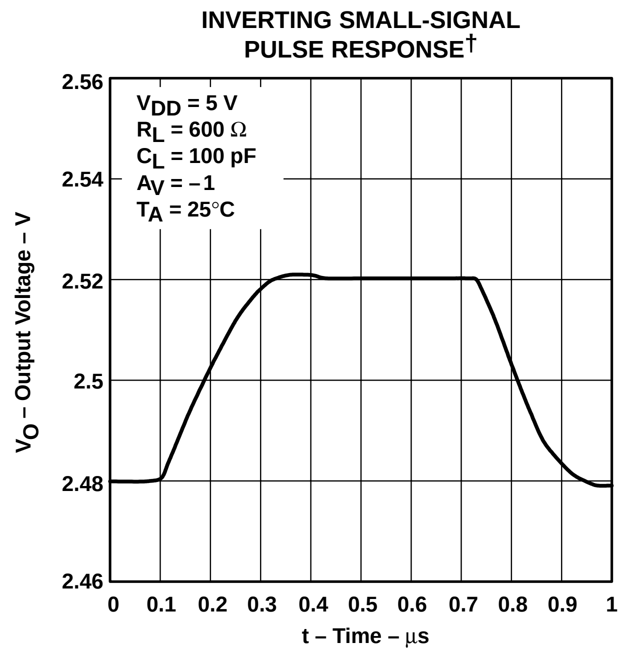


Figure 41

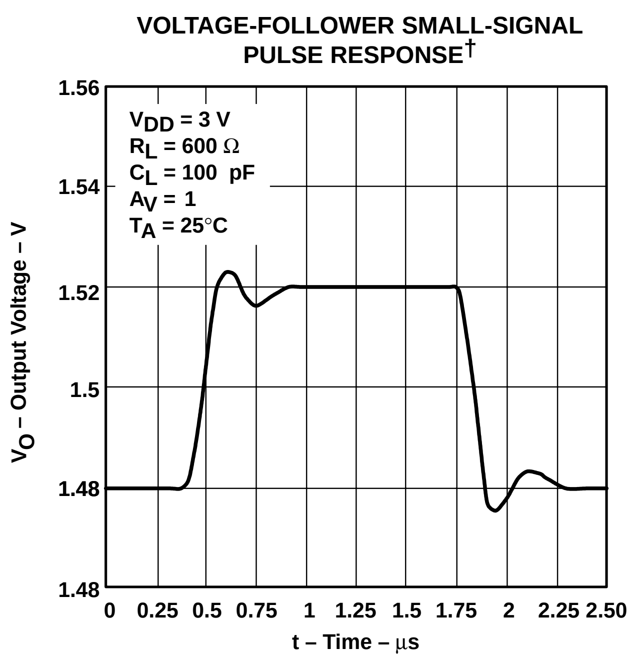


Figure 42

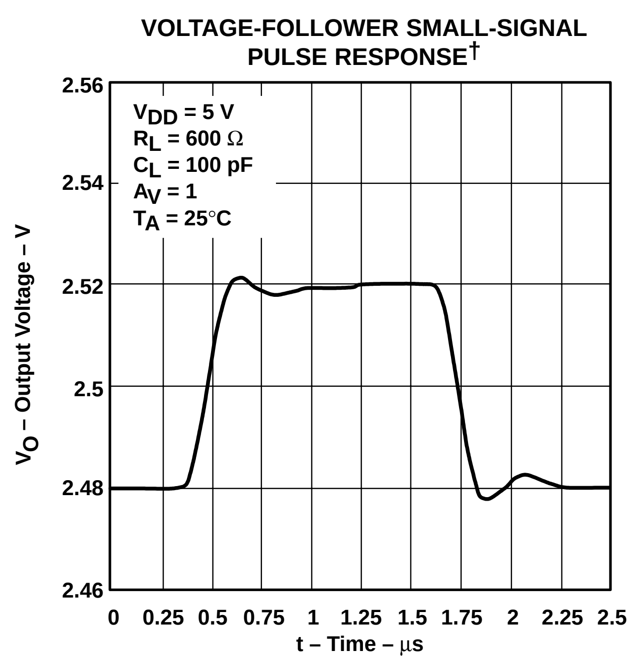


Figure 43

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

EQUIVALENT INPUT NOISE VOLTAGE†
vs
FREQUENCY

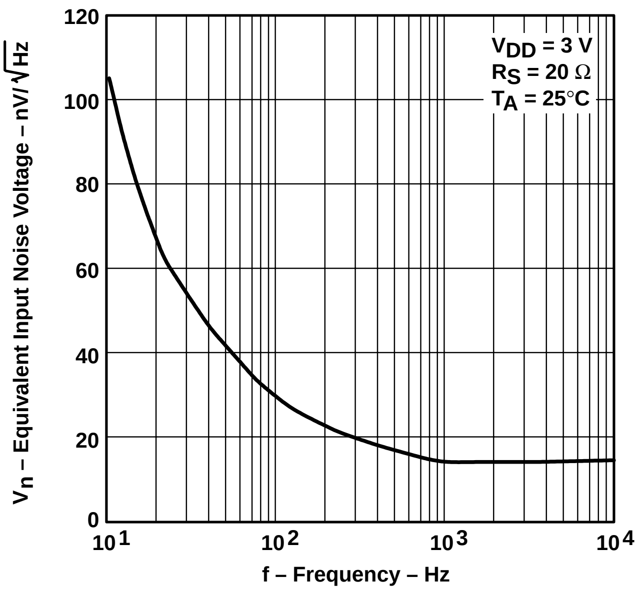


Figure 44

EQUIVALENT INPUT NOISE VOLTAGE†
vs
FREQUENCY

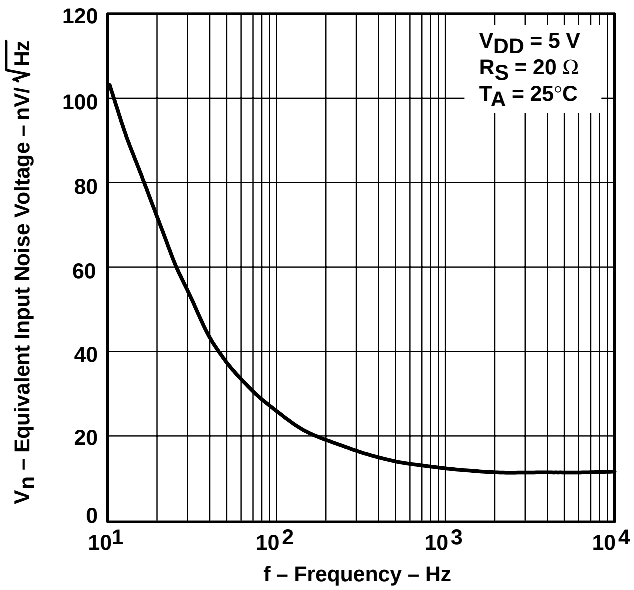


Figure 45

INPUT NOISE VOLTAGE OVER
A 10-SECOND PERIOD†

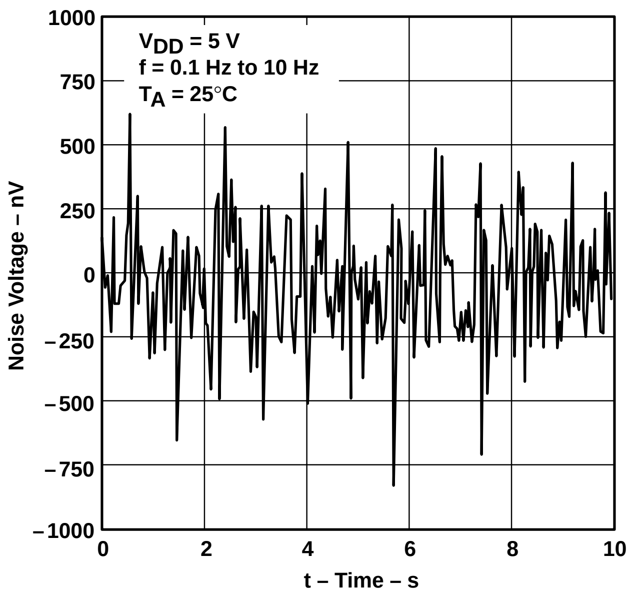


Figure 46

TOTAL HARMONIC DISTORTION PLUS NOISE†
vs
FREQUENCY

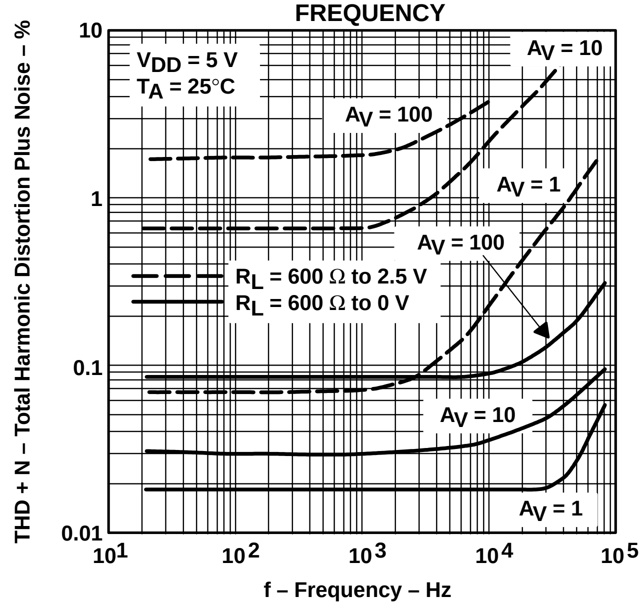


Figure 47

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

GAIN-BANDWIDTH PRODUCT †‡
vs
FREE-AIR TEMPERATURE

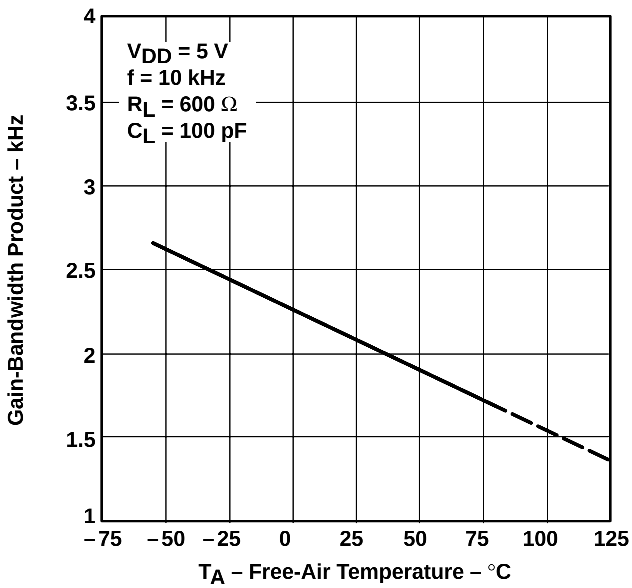


Figure 48

GAIN-BANDWIDTH PRODUCT ‡
vs
SUPPLY VOLTAGE

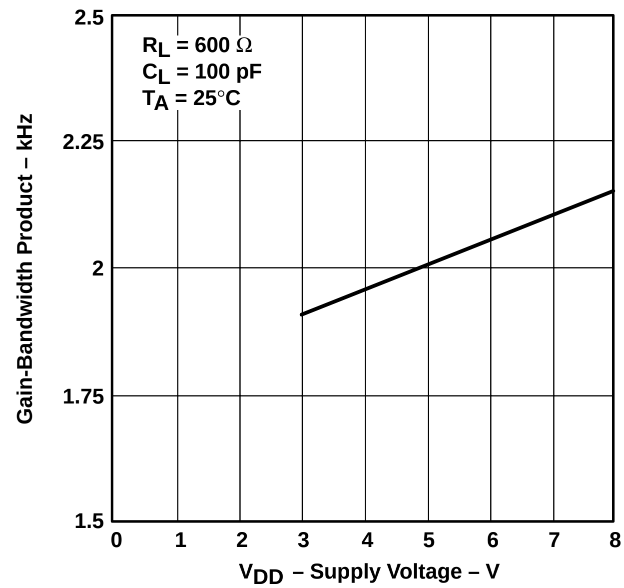


Figure 49

GAIN MARGIN‡
vs
LOAD CAPACITANCE

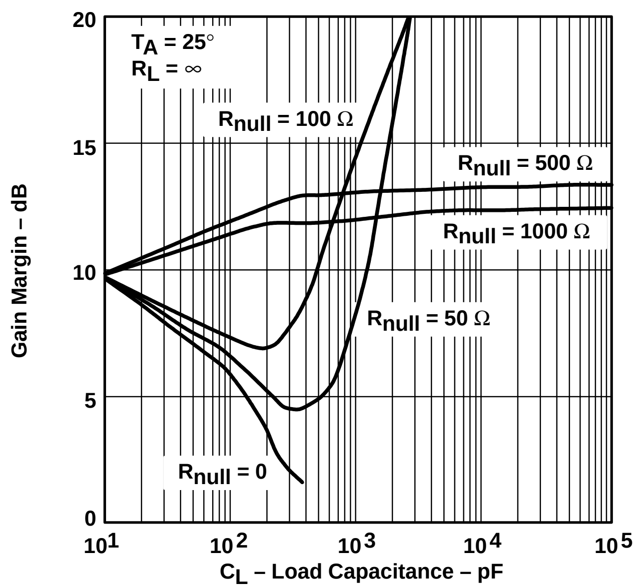


Figure 50

GAIN MARGIN‡
vs
LOAD CAPACITANCE

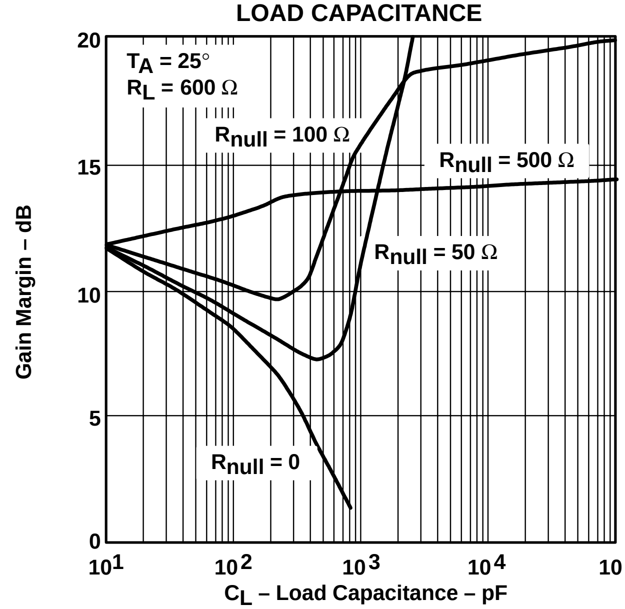


Figure 51

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

PHASE MARGIN†
vs
LOAD CAPACITANCE

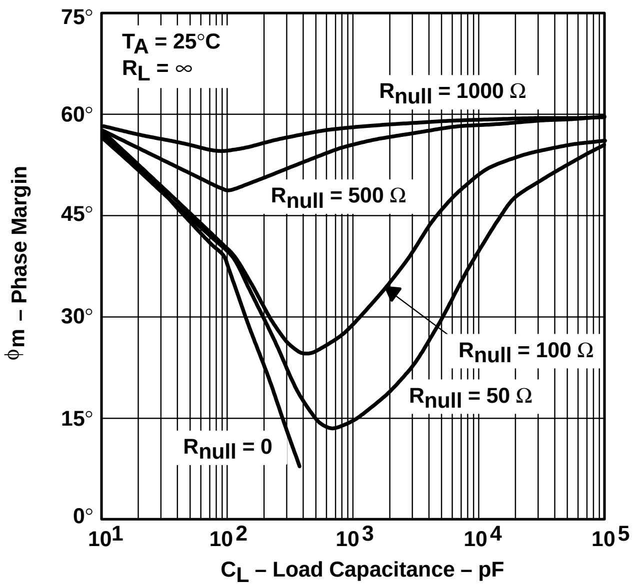


Figure 52

PHASE MARGIN†
vs
LOAD CAPACITANCE

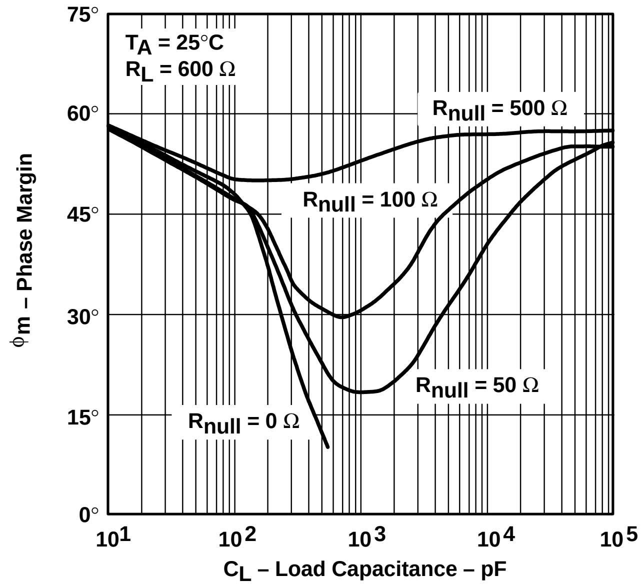


Figure 53

UNITY-GAIN BANDWIDTH†
vs
LOAD CAPACITANCE

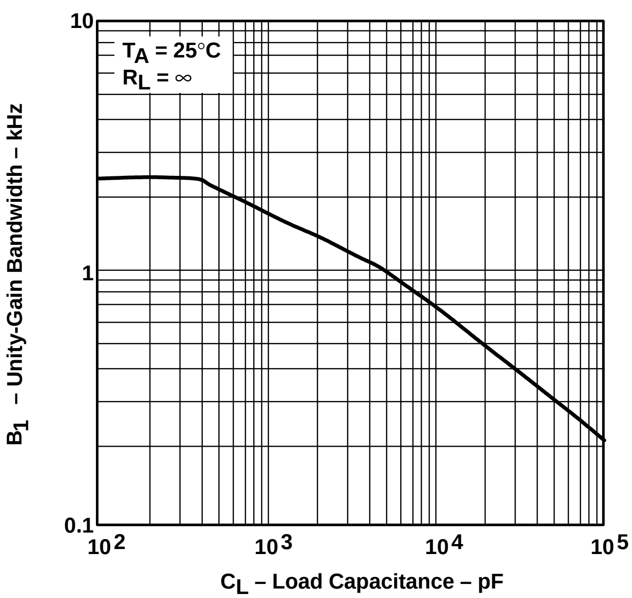


Figure 54

UNITY-GAIN BANDWIDTH†
vs
LOAD CAPACITANCE

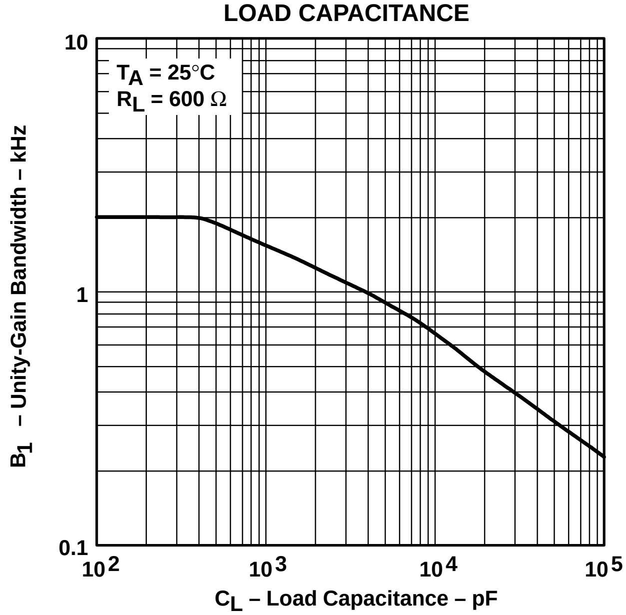


Figure 55

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

APPLICATION INFORMATION

driving large capacitive loads

The TLV2231 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 through Figure 55 illustrate its ability to drive loads greater than 100 pF while maintaining good gain and phase margins (R_{null} = 0).

A small series resistor (R_{null}) at the output of the device (see Figure 56) improves the gain and phase margins when driving large capacitive loads. Figure 50 through Figure 53 show the effects of adding series resistances of 50 Ω, 100 Ω, 500 Ω, and 1000 Ω. The addition of this series resistor has two effects: the first effect is that it adds a zero to the transfer function and the second effect is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the approximate improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1}\left(2 \times \pi \times UGBW \times R_{null} \times C_L\right) \tag{1}$$

Where :

$\Delta\phi_{m1}$ = Improvement in phase margin

UGBW = Unity – gain bandwidth frequency

R_{null} = Output series resistance

C_L = Load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 54 and Figure 55). To use equation 1, UGBW must be approximated from Figure 54 and Figure 55.

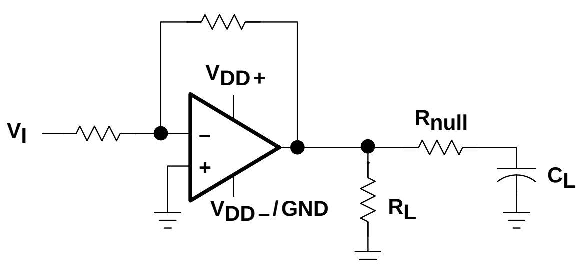


Figure 56. Series-Resistance Circuit

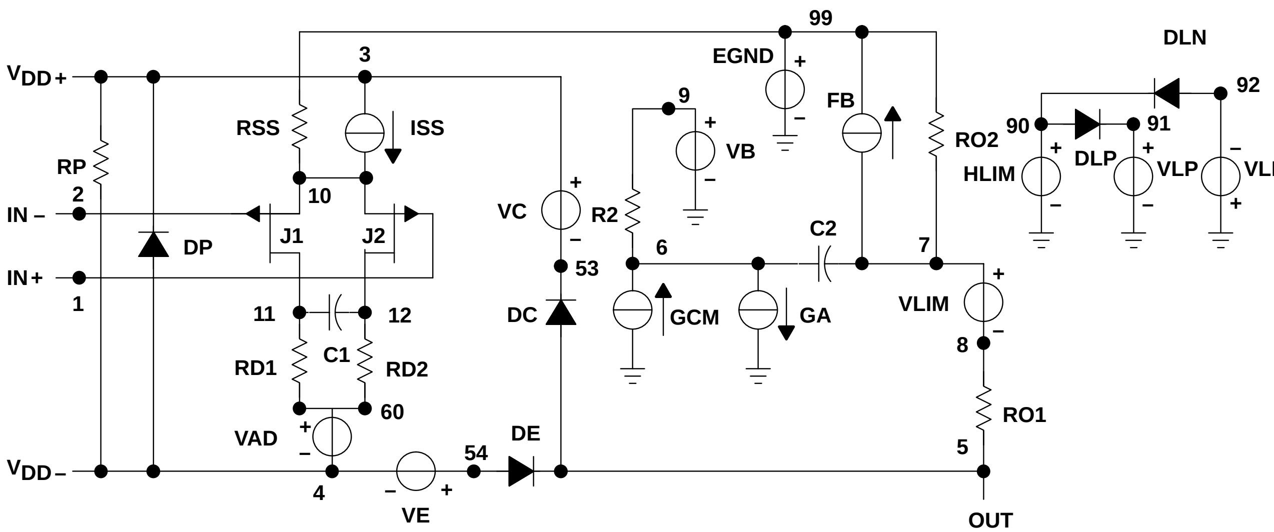
APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 6) and subcircuit in Figure 57 are generated using the TLV2231 typical electrical and operating characteristics at T_A = 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, “Macromodeling of Integrated Circuit Operational Amplifiers,” *IEEE Journal of Solid-State Circuits,* SC-9, 353 (1974).




```
.SUBCKT TLV2231 1 2 3 4 5
     C1     11   12   13.51E–12
     C2     6    7    50.00E–12
     DC     5    53   DX
     DE     54   5    DX
     DLP    90   91   DX
     DLN    92   90   DX
     DP     4    3    DX
     EGND   99   0    POLY (2) (3,0) (4,0) 0 .5 .5
     FB     7    99   POLY (5) VB VC VE VLP
     + VLN 0 90.83E3 –10E3 10E3 10E3 –10E3
     GA     6    0    11   12 314.2E–6
     GCM    0    6    10   99 242.35E–9
     ISS    3    10   DC   87.00E–6
     HLIM   90   0    VLIM 1K
     J1     11   2    10 JX
     J2     12   1    10 JX
     R2     6    9    100.0E3
     RD1    60   11   3.183E3
     RD2    60   12   3.183E3
     R01    8    5    25
     R02    7    99   25
     RP     3    4    6.553E3
     RSS    10   99   2.500E6
     VAD    60   4    –.5
     VB     9    0    DC 0
     VC     3    53   DC .795
     VE     54   4    DC .795
     VLIM   7    8    DC 0
     VLP    91   0    DC 12.4
     VLN    0    92   DC 17.4
.MODEL DX D (IS=800.0E–18)
.MODEL JX PJF (IS=500.0E–15 BETA=2.939E–3
+ VTO=–.065)
.ENDS
```

Figure 57. Boyle Macromodel and Subcircuit

PSpice and *Parts* are trademark of MicroSim Corporation.

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
TLV2231CDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231CDBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231CDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231CDBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231IDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231IDBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231IDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2231IDBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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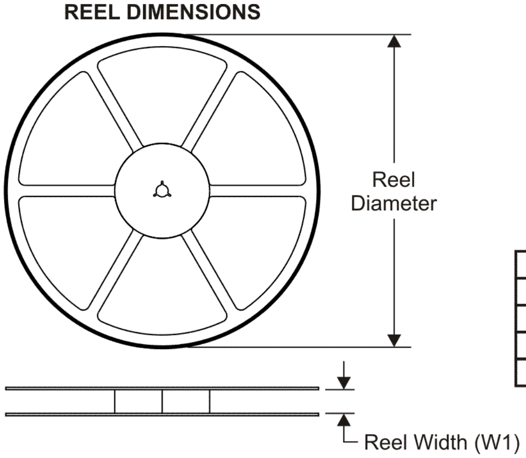
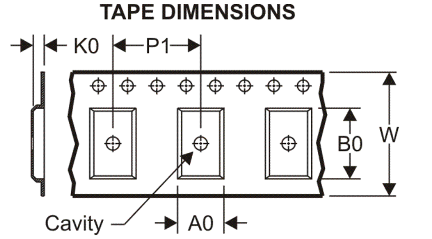
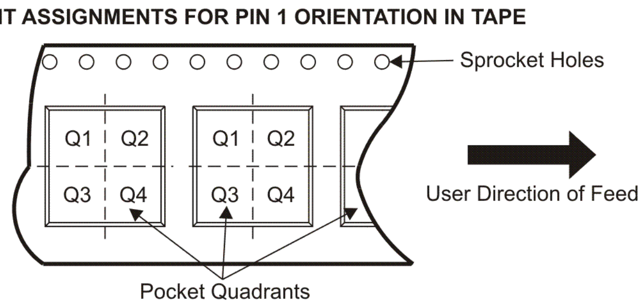
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION





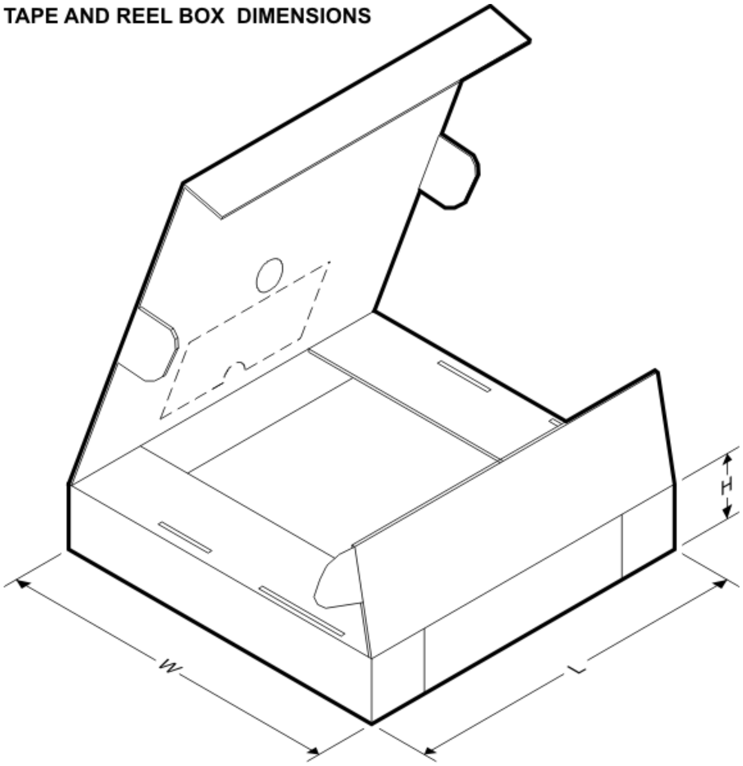
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2231CDBVR	SOT-23	DBV	5	3000	180.0	9.0	3.15	3.2	1.4	4.0	8.0	Q3
TLV2231CDBVT	SOT-23	DBV	5	250	180.0	9.0	3.15	3.2	1.4	4.0	8.0	Q3
TLV2231IDBVR	SOT-23	DBV	5	3000	180.0	9.0	3.15	3.2	1.4	4.0	8.0	Q3
TLV2231IDBVT	SOT-23	DBV	5	250	180.0	9.0	3.15	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2231CDBVR	SOT-23	DBV	5	3000	182.0	182.0	20.0
TLV2231CDBVT	SOT-23	DBV	5	250	182.0	182.0	20.0
TLV2231IDBVR	SOT-23	DBV	5	3000	182.0	182.0	20.0
TLV2231IDBVT	SOT-23	DBV	5	250	182.0	182.0	20.0